ABSTRACT OF THE DISCLOSURE

The present invention discloses a method of manufacturing an active matrix display device, comprising: a) forming a semiconductor layer on an insulating substrate; b) forming a gate insulating layer over the whole surface of the substrate while convering the semiconductor layer; c) forming a gate electrode on the gate insulating layer over the semiconductor layer; d) forming spacers on both side wall portions of the gate electrode while exposing both end portions of the semiconductor layer; e) ion-implaing a high-density impurity into the semiconductor layer to form high-density source and drain regions in the semiconductor layer; f) depositing sequentially a transparent conductive layer and a metal layer on the inter insulating layer; g) patterning the transparent conductive layer and the metal layer to form the source and drain electrodes, the source and drain electrodes directly contacting the high-density source and drain regions and having a dual-layered structure; h) forming a passivation layer over the whole surface of the substrate; i) etching the passivation layer and the metal layer to form an opening portion exposing a portions of the transparent conductive layer, thereby forming a pixel electrode; and j) performing a reflow process to cover the metal layer in the opening portion by the passivation layer.